

Si APD



S14643-02

High speed, compact Si APD for LiDAR (700 nm band) featuring low-bias operation

The S14643 02 is a compact, surface mount type Si APD that achieves high sensitivity in the 700 nm band. This is suitable for laser monitoring of optical rangefinders widely used from consumer electronics to industrial use.

Features

- Small package: 3.1 × 1.8 × 1.0^t mm
- → Peak sensitivity wavelength: 760 nm (M=100)
- **Low-bias operation: Breakdown voltage=120 V max.**
- → High-speed response: Cutoff frequency=2 GHz typ.
 - (λ=760 nm, M=100)
- Reduction of breakdown voltage variation 100 ± 20 V

Applications

Optical rangefinders

Structure

Parameter	Specification	Unit
Photosensitive area*1	ф0.2	mm
Effective photosensitive area	0.03	mm ²
Package	Glass epoxy (silicone resin)	-

^{*1:} Area in which a typical gain can be obtained

- Absolute maximum ratings

Parameter	Symbol	Specification	
Reverse current (DC)	Ir max	0.2	mA
Forward current	IF max	10	mA
Operating temperature*2	Topr	-30 to +100	°C
Storage temperature*2	Tstg	-40 to +100	°C
Soldering temperature	Tsol	260 (3 times)*3	°C

^{*2:} No dew condensation

When there is a temperature difference between a product and the surrounding area in high humidity environments, dew condensation may occur on the product surface. Dew condensation on the product may cause deterioration in characteristics and reliability.

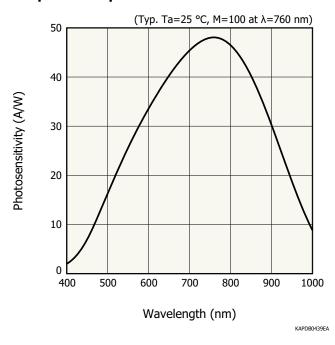
Note: Exceeding the absolute maximum ratings even momentarily may cause a drop in product quality. Always be sure to use the product within the absolute maximum ratings.

^{*3:} Reflow soldering, JEDEC J-STD-020 MSL 2a, see P.5

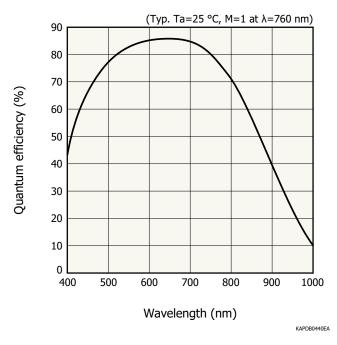
➡ Electrical and optical characteristics (Ta=25 °C)

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
Spectral response range	λ		400 to 1000			nm
Peak sensitivity wavelength	λр		-	760	-	nm
Photosensitivity	S	λ=760 nm, M=1	-	0.48	-	A/W
Quantum efficiency	QE	λ=760 nm, M=1	-	78	-	%
Breakdown voltage	VBR	ID=100 μA	80	100	120	V
Temperature coefficient of breakdown voltage	ΔTVBR		-	0.42	-	V/°C
Dark current	ID	M=100	-	20	200	pA
Temperature coefficient of dark current	ΔTid	M=100	-	1.1	-	times/°C
Cutoff frequency	fc	M=100, RL=50 Ω λ=760 nm, -3 dB	-	2	-	GHz
Terminal capacitance	Ct	M=100, f=1 MHz	-	0.7	-	pF
Excess noise figure	Х	M=100, λ=760 nm	-	0.3	-	-
Gain	М	λ=760 nm	-	100	-	-

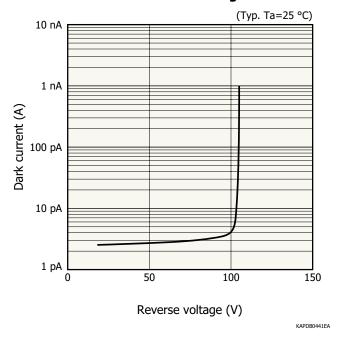
Spectral response



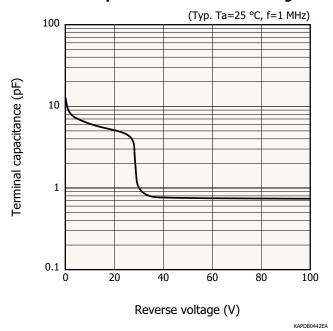
- Quantum efficiency vs. wavelength



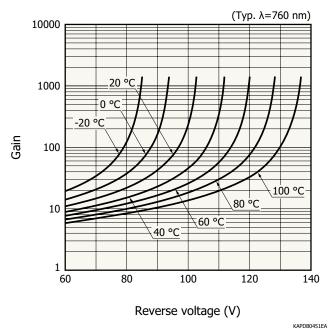
Dark current vs. reverse voltage



Terminal capacitance vs. reverse voltage

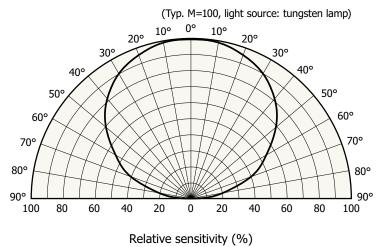


Gain vs. reverse voltage



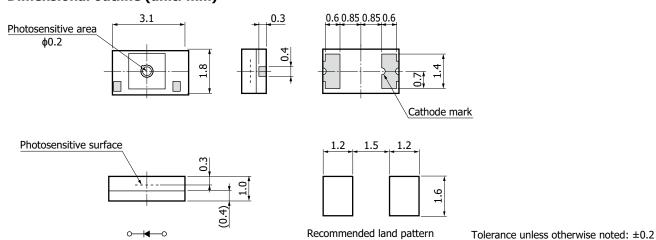


Directivity



KAPDB0450EA

► Dimensional outline (unit: mm)



Position accuracy of photosensitive area: X, Y≤±0.2

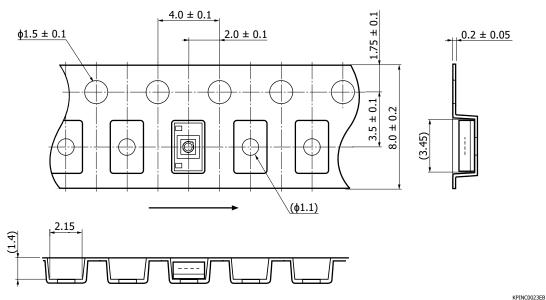
KAPDA0203EA

Standard packing specifications

■ Reel (conforms to JEITA ET-7200)

Outer diameter	Hub diameter	Tape width	Material	Electrostatic characteristics
ф180 mm	ф60 mm	8 mm	PS	Conductive

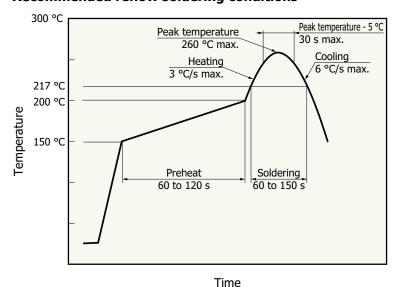
■ Embossed tape (unit: mm, material: PS, conductive)



- Packing quantity 2000 pcs/reel
- Packing type

 Reel and desiccant in moisture-proof packaging (vacuum-sealed)

Recommended reflow soldering conditions



- After unpacking, store the device in an environment at a temperature of 30 °C or less and a humidity of 60% or less, and perform reflow soldering within 4 weeks.
- The effect that the product receives during reflow soldering varies depending on the circuit board and the reflow oven that are used. When you set reflow soldering conditions, check that problems do not occur in the product by testing out the conditions in advance.

KMPDB0405EC

Related information

www.hamamatsu.com/sp/ssd/doc_en.html

- Precautions
- Disclaimer
- · Precautions / Surface mount type products
- Catalog
- · Technical note / Si photodiodes

Information described in this material is current as of January 2025.

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HAMAMATSU PHOTONICS K.K., Solid State Division

1126-1 Ichino-cho, Chuo-ku, Hamamatsu City, 435-8558 Japan, Telephone: (81)53-434-3311, Fax: (81)53-434-5184

ILIZO-I ICRIINO-CRO, CRUO-KU, Hamamatsu City, 435-858 Japan, Ielephone: (1)908-2(31-1956), Fax: (1)908-231-1956), Fax: (1)908-231-1956), Fax: (1)908-231-1956), Fax: (1)908-231-1956), Fax: (1)908-231-1956), Fax: (1)908-231-1956), Fax: (2)908-231-1956), Fax: (3)918-23-75-0, Fax: (4)98152-265-8 E-mail: info@hamamatsu.de France: HAMAMATSU PHOTONICS FRANCE S.A.R.L.: 19 Rue du Saule Trapu, Parc du Moulin de Massy, 91882 Massy Cedex, France; Telephone: (3)11 69 53 71 00, Fax: (33)1 69 53 71 10 E-mail: info@hamamatsu.df United Kingdom: HAMAMATSU PHOTONICS IX LIMITED: 2 Howard Court, 10 Tewin Road, Welwyn Garden City, Hertfordshire, AL7 18W, UK, Telephone: (44)1707-2925777 E-mail: info@hamamatsu.co.uk North Europe: HAMAMATSU PHOTONICS NORDEN AB: Torshamnsgatan 35, 16440 Kista, Sweden, Telephone: (46)8-509-031-00, Fax: (46)8-509-031-01 E-mail: info@hamamatsu.de Italy: HAMAMATSU PHOTONICS ITALIA S.R.L.: Strada della Moia, 1 int. 6 20044 Arese (Milano), Italy, Telephone: (46)8-509-031-01 E-mail: info@hamamatsu.it inf